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1N485B & 1N486B Small Signal Diode

Features:

- DO-35 Package

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$, Note 1 unless otherwise specified)

Max. Repetitive Reverse Voltage, V_{RRM}		
1N485B	200V	
1N486B	250V	
Power Dissipation, P_D	500mW	
Average Rectified Forward Current, $I_{F(AV)}$	200mA	
None-Repetitive Forward Surge Current, I_{FSM}		
Pulse Width = 10.0 seconds	1.0A	
Pulse Width = 1.0 microsecond	4.0A	
Operating Junction Temperature, T_J	175°C	
Storage Temperature Range, T_{stg}	-65° to +200°C	
Thermal Resistance, Junction to Ambient, R_{thJA}	+300°C/W	

Note 1. These ratings are limiting values above which the serviceability of the device may be impaired.

Note 2. These ratings are based on a maximum junction temperature of +200°C.

Note 3. These are steady state limits.

Electrical Characteristics: ($T_A = +25^\circ\text{C}$, unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Breakdown Voltage 1N485B	V_R	$I_R = 5\mu\text{A}$	200	-	-	V
		$I_R = 100\mu\text{A}$	250	-	-	V
1N486B						
Forward Voltage	V_F	$I_F = 100\text{mA}$	-	-	1.0	V
Reverse Leakage 1N485B	I_R	$V_R = 175\text{V}$	-	-	25	μA
		$V_R = 175\text{V}, T_A = 150^\circ\text{C}$	-	-	5	μA
1N486B	I_R	$V_R = 225\text{V}$	-	-	50	μA
		$V_R = 225\text{V}, T_A = 150^\circ\text{C}$	-	-	10	μA

